

SN54HC10, SN74HC10 TRIPLE 3-INPUT POSITIVE-NAND GATES

SCLS083A – DECEMBER 1982 – REVISED JANUARY 1996

- Package Options Include Plastic Small-Outline (D) and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Standard Plastic (N) and Ceramic (J) 300-mil DIPs

description

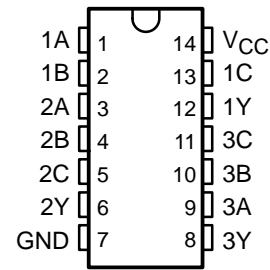
These devices contain three independent 3-input NAND gates. They perform the Boolean function $Y = A \cdot B \cdot C$ or $Y = A + B + C$ in positive logic.

The SN54HC10 is characterized for operation over the full military temperature range of -55°C to 125°C . The SN74HC10 is characterized for operation from -40°C to 85°C .

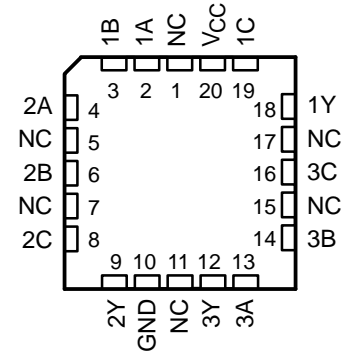
FUNCTION TABLE
(each gate)

INPUTS			OUTPUT Y
A	B	C	
H	H	H	L
L	X	X	H
X	L	X	H
X	X	L	H

SN54HC10 . . . J OR W PACKAGE
SN74HC10 . . . D OR N PACKAGE
(TOP VIEW)

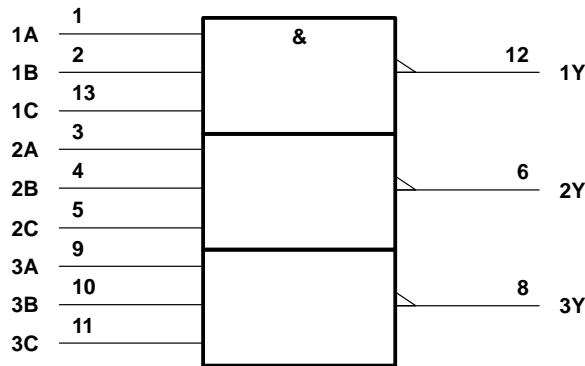


SN54HC10 . . . FK PACKAGE
(TOP VIEW)



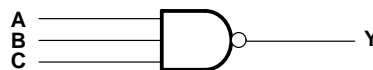
NC – No internal connection

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. Pin numbers shown are for the D, J, N, and W packages.

logic diagram (positive logic)



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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

**TEXAS
INSTRUMENTS**

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SN54HC10, SN74HC10

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absolute maximum ratings over operating free-air temperature range†

Supply voltage range, V_{CC}	–0.5 V to 7 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) (see Note 1)	±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) (see Note 1)	±20 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC})	±25 mA
Continuous current through V_{CC} or GND	±50 mA
Maximum power dissipation at $T_A = 55^\circ\text{C}$ (in still air) (see Note 2): D package	1.25 W
N package	1.1 W
Storage temperature range, T_{stg}	–65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils, except for the N package, which has a trace length of zero.

recommended operating conditions

			SN54HC10			SN74HC10			UNIT
			MIN	NOM	MAX	MIN	NOM	MAX	
V _{CC}	Supply voltage		2	5	6	2	5	6	V
V _{IH}	High-level input voltage	V _{CC} = 2 V	1.5			1.5			V
		V _{CC} = 4.5 V	3.15			3.15			
		V _{CC} = 6 V	4.2			4.2			
V _{IL}	Low-level input voltage	V _{CC} = 2 V	0			0			V
		V _{CC} = 4.5 V	0			1.35			
		V _{CC} = 6 V	0			1.8			
V _I	Input voltage		0		V _{CC}	0		V _{CC}	V
V _O	Output voltage		0		V _{CC}	0		V _{CC}	V
t _t	Input transition (rise and fall) time	V _{CC} = 2 V	0		1000	0		1000	ns
		V _{CC} = 4.5 V	0		500	0		500	
		V _{CC} = 6 V	0		400	0		400	
T _A	Operating free-air temperature		−55		125	−40		85	°C

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V _{CC}	T _A = 25°C			SN54HC10		SN74HC10		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V _{OH}	V _I = V _{IH} or V _{IL}	I _{OH} = -20 µA	2 V	1.9	1.998		1.9		1.9		V
			4.5 V	4.4	4.499		4.4		4.4		
			6 V	5.9	5.999		5.9		5.9		
		I _{OH} = -4 mA	4.5 V	3.98	4.3		3.7		3.84		
		I _{OH} = -5.2 mA	6 V	5.48	5.8		5.2		5.34		
V _{OL}	V _I = V _{IH} or V _{IL}	I _{OL} = 20 µA	2 V		0.002	0.1		0.1		0.1	V
			4.5 V		0.001	0.1		0.1		0.1	
			6 V		0.001	0.1		0.1		0.1	
		I _{OL} = 4 mA	4.5 V		0.17	0.26		0.4		0.33	
		I _{OL} = 5.2 mA	6 V		0.15	0.26		0.4		0.33	
I _I	V _I = V _{CC} or 0		6 V		±0.1	±100		±1000		±1000	nA
I _{CC}	V _I = V _{CC} or 0, I _O = 0		6 V			2		40		20	µA
C _i			2 V to 6 V		3	10		10		10	pF

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC}	T _A = 25°C			SN54HC10		SN74HC10		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A, B, or C	Y	2 V		35	95		145		120	ns
			4.5 V		10	19		29		24	
			6 V		9	16		25		20	
t _t		Y	2 V		23	75		110		95	ns
			4.5 V		6	15		22		19	
			6 V		5	13		19		16	

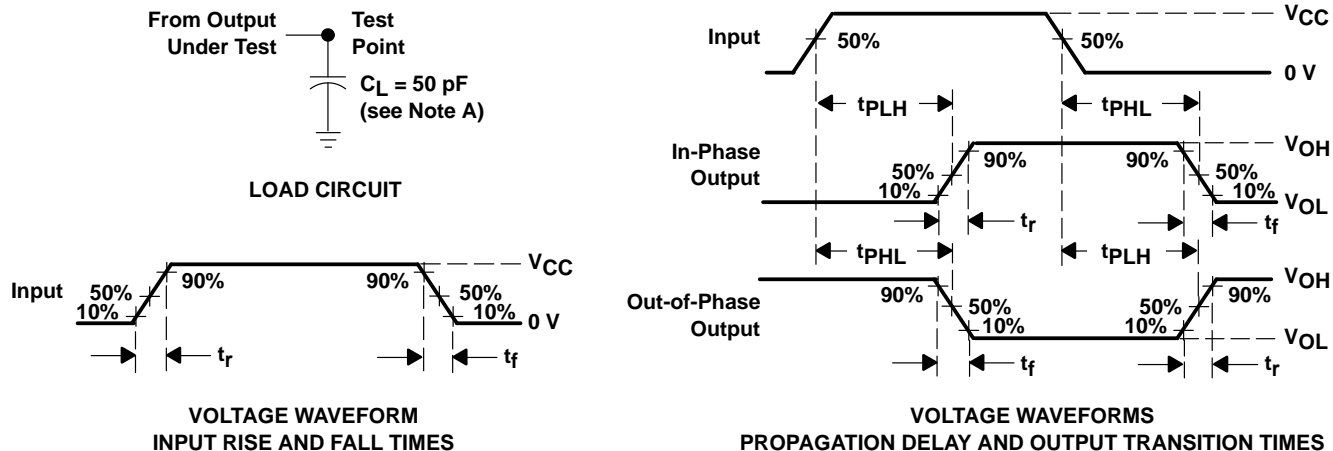
operating characteristics, T_A = 25°C

PARAMETER	TEST CONDITIONS	TYP	UNIT
C _{pd} Power dissipation capacitance per gate	No load	25	pF

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PARAMETER MEASUREMENT INFORMATION



- NOTES: A. C_L includes probe and test-fixtue capacitance.
 B. Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: $PRR \leq 1 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r = 6 \text{ ns}$, $t_f = 6 \text{ ns}$.
 C. The outputs are measured one at a time with one input transition per measurement.
 D. t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 1. Load Circuit and Voltage Waveforms

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